WHAT IS CLAIMED IS:

1. A current-perpendicular-to-the-plane structure magnetoresistive element comprising:

a lower portion of a magnetoresistive film extending over a surface of a lower electrode layer by a first width in a lateral direction;

an upper portion of the magnetoresistive film extending over a surface of the lower portion by a second width smaller than the first width in the lateral direction;

insulators sandwiching the upper portion of the magnetoresistive film in the lateral direction;

domain control magnetic layers sandwiching the upper portion of the magnetoresis tive film and the insulators in the lateral direction; and

an upper electrode layer contacting the upper portion of the magnetoresistive film.

- 2. The current-perpendicular-to-the-plane structure magnetoresistive element according to claim 1, wherein said insulator is a magnetic.
- 3. The current perpendicular-to-the-plane structure magnetoresistive element according to claim 1, wherein said upper portion of the magnetoresistive film includes a free magnetic layer.
- 4. A method of making a current-perpendicular-to-theplane structure magnetoresistive element, comprising:

forming a magnetoresistive film on a surface of a lower electrode layer;

forming a pair of domain control magnetic layers

sandwiching the magnetoresistive film;

forming an insulator film covering over the domain control magnetic layers; and

subjecting an upper surface of the magnetoresistive film to an etching process.

- 5. The method according to claim 4, wherein said insulator film remains on the/domain control magnetic layers after the etching process.
- 6. The method according to claim 5, wherein grooves are formed between the magnetoresistive film and the respective domain control/magnetic layers based on the etching process.
- 7. The method according to claim 6, wherein an insulator is filled in the groove.
- 8. The method according to claim 7, wherein said magnetor sistive film includes a free magnetic layer located between the insulators.
- . The method according to claim 8, wherein said insulator is a magnetic.